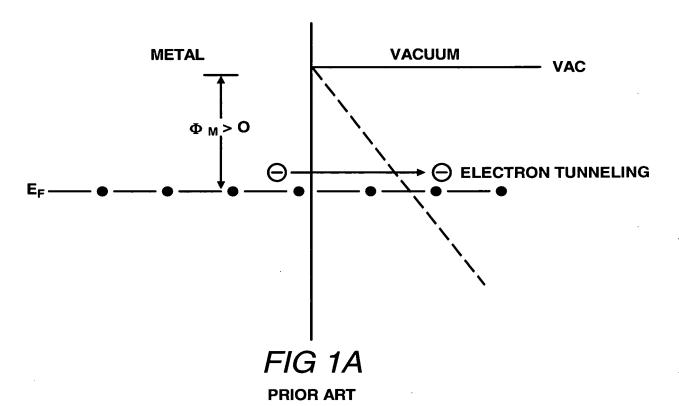
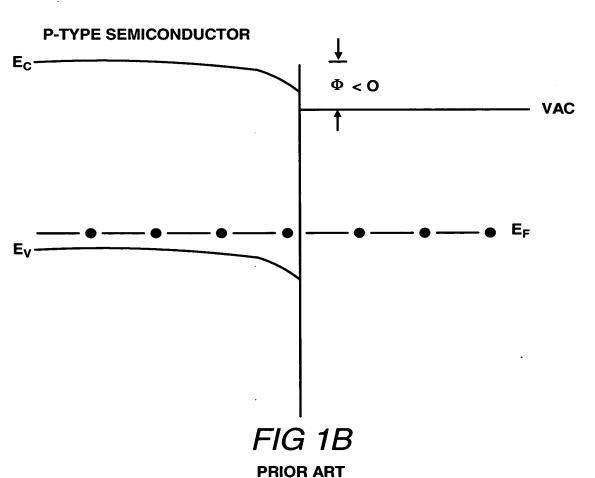


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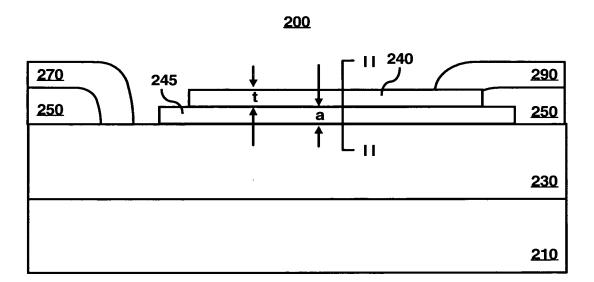


FIG 2A

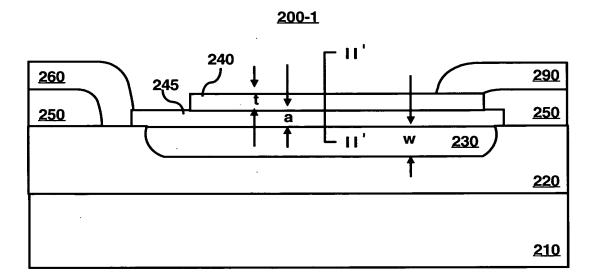


FIG 2B



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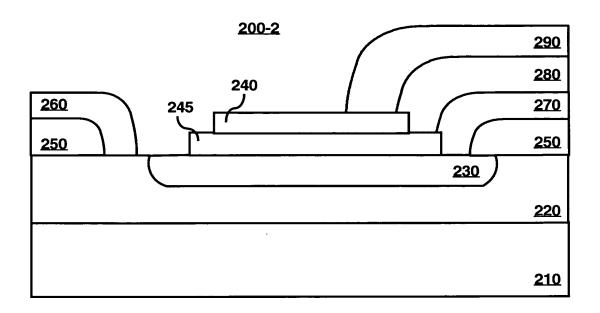
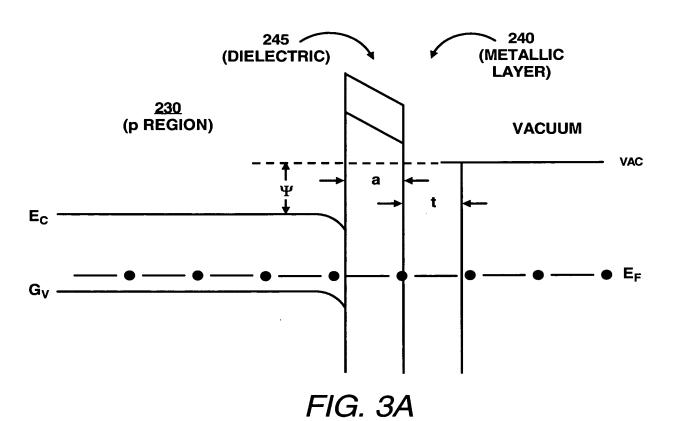
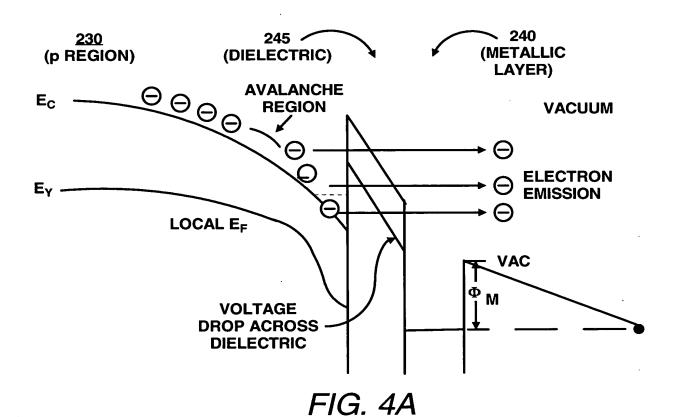


FIG 2C



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